

# Yoon Jang Chung

## List of Publications by Year in descending order

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papers

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all docs

39  
docs citations

39  
times ranked

997  
citing authors

#	ARTICLE	IF	CITATIONS
1	Correlated States of 2D Electrons near the Landau Level Filling $\nu = 1/2$ . Physical Review Letters, 2022, 128, 026802.	7.8	8
2	Record-quality GaAs two-dimensional hole systems. Physical Review Materials, 2022, 6, .	2.4	12
3	Ultra-high-quality two-dimensional electron systems. Nature Materials, 2021, 20, 632-637.	27.5	76
4	Heterostructure design to achieve high quality, high density GaAs 2D electron system with g-factor tending to zero. Applied Physics Letters, 2020, 117, 022102.	3.3	0
5	Observation of spontaneous ferromagnetism in a two-dimensional electron system. Proceedings of the National Academy of Sciences of the United States of America, 2020, 117, 32244-32250.	7.1	28
6	Working principles of doping-well structures for high-mobility two-dimensional electron systems. Physical Review Materials, 2020, 4, .	2.4	18
7	Spatial Mapping of Local Density Variations in Two-dimensional Electron Systems Using Scanning Photoluminescence. Nano Letters, 2019, 19, 1908-1913.	9.1	7
8	Surface segregation and the Al problem in GaAs quantum wells. Physical Review Materials, 2018, 2, .	2.4	14
9	Multivalley two-dimensional electron system in an AlAs quantum well with mobility exceeding $0.16 \text{ cm}^2/\text{Vs}$ .	2.4	16
10	Design rules for modulation-doped AlAs quantum wells. Physical Review Materials, 2017, 1, .	2.4	16
11	Effects of substrate conductivity on cell morphogenesis and proliferation using tailored, atomic layer deposition-grown ZnO thin films. Scientific Reports, 2015, 5, 9974.	3.3	26
12	Nano-glass frit for inkjet printed front side metallization of silicon solar cells prepared by sol-gel process. Physica Status Solidi - Rapid Research Letters, 2015, 9, 293-296.	2.4	4
13	Indium tin oxide/InGaZnO bilayer stacks for enhanced mobility and optical stability in amorphous oxide thin film transistors. Applied Physics Letters, 2014, 105, .	3.3	24
14	A Simple Method for Cleaning Graphene Surfaces with an Electrostatic Force. Advanced Materials, 2014, 26, 637-644.	21.0	25
15	Growth of p-Type Tin(II) Monoxide Thin Films by Atomic Layer Deposition from Bis(1-dimethylamino-2-methyl-2-propoxy)tin and $\text{H}_2\text{O}$ . Chemistry of Materials, 2014, 26, 6088-6091.	6.7	76
16	A study on the influence of local doping in atomic layer deposited Al:ZnO thin film transistors. Journal of Materials Chemistry C, 2014, 2, 9274-9282.	5.5	21
17	Fabrication of free-standing $\text{Al}_2\text{O}_3$ nanosheets for high mobility flexible graphene field effect transistors. Journal of Materials Chemistry C, 2014, 2, 4759.	5.5	4
18	Synthesis of nitrogen doped graphite oxide and its electrochemical properties. Current Applied Physics, 2014, 14, 82-86.	2.4	27

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19	Trimethylsilylcyclopentadienyl tris(dimethylamino)zirconium as a single-source metal precursor for the atomic layer deposition of $Zr_xSi_{1-x}O_4$ . <i>Thin Solid Films</i> , 2014, 564, 140-145.	1.8	2
20	Drawing Circuits with Carbon Nanotubes: Scratch-Induced Graphoepitaxial Growth of Carbon Nanotubes on Amorphous Silicon Oxide Substrates. <i>Scientific Reports</i> , 2014, 4, 5289.	3.3	11
21	Study on the defects in metal-organic chemical vapor deposited zinc tin oxide thin films using negative bias illumination stability analysis. <i>Journal of Materials Chemistry C</i> , 2013, 1, 6695.	5.5	18
22	The Electrical Properties of Asymmetric Schottky Contact Thin-Film Transistors with Amorphous- $In_2Ga_2ZnO_7$ . <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 1128-1135.	3.0	18
23	The charge trapping characteristics of $Si_3N_4$ and $Al_2O_3$ layers on amorphous-indium-gallium-zinc oxide thin films for memory application. <i>Applied Physics Letters</i> , 2012, 100, 183503.	3.3	20
24	Optical modeling and experimental verification of light induced phenomena in In-Ga-Zn-O thin film transistors with varying gate insulator thickness. <i>Journal of Applied Physics</i> , 2012, 111, 024511.	2.5	8
25	Vertically integrated submicron amorphous- $In_2Ga_2ZnO_7$ thin film transistor using a low temperature process. <i>Applied Physics Letters</i> , 2012, 100, 203510.	3.3	34
26	Properties of Atomic Layer Deposited $HfO_2$ Films on Ge Substrates Depending on Process Temperatures. <i>Journal of the Electrochemical Society</i> , 2012, 159, G33-G39.	2.9	16
27	The Impact of Carbon Concentration on the Crystalline Phase and Dielectric Constant of Atomic Layer Deposited $HfO_2$ Films on Ge Substrate. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, N33-N37.	1.8	25
28	Reduction of Charge Trapping in $HfO_2$ Film on Ge Substrates by Atomic Layer Deposition of Various Passivating Interfacial Layers. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 2350-2356.	3.0	12
29	Performance Variation According to Device Structure and the Source/Drain Metal Electrode of a-IGZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2012, 59, 3357-3363.	3.0	34
30	Resistive Switching in $TiO_2$ Thin Films Using the Semiconducting In-Ga-Zn-O Electrode. <i>IEEE Electron Device Letters</i> , 2012, 33, 582-584.	3.9	10
31	Correlation of the change in transfer characteristics with the interfacial trap densities of amorphous $InGaZnO$ thin film transistors under light illumination. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	59
32	Improvement in the negative bias illumination temperature stress instability of $InGaZnO$ thin film transistors using an $Al_2O_3$ buffer layer. <i>Physica Status Solidi - Rapid Research Letters</i> , 2011, 5, 178-180.	2.4	15
33	The effects of device geometry on the negative bias temperature instability of Hf-In-Zn-O thin film transistors under light illumination. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	16
34	Direct Observation of Hole Current in Amorphous Oxide Semiconductors under Illumination. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, G35.	2.2	12
35	Study on the Existence of Abnormal Hysteresis in Hf-In-Zn-O Thin Film Transistors under Illumination. <i>Electrochemical and Solid-State Letters</i> , 2011, 14, H300.	2.2	15
36	Amorphous Oxide Semiconductor Memory Using High- $k$ Charge Trap Layer. <i>ECS Transactions</i> , 2010, 33, 375-380.	0.5	0

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37	The Effect of Light Illumination on Transfer Curve and Stability of Amorphous Hf-In-ZnO Thin Film Transistors. ECS Transactions, 2010, 33, 319-324.	0.5	0
38	The Effect of Illumination on the Negative Bias Temperature Instability in Zinc Tin Oxide Thin Film Transistors. ECS Transactions, 2010, 33, 325-330.	0.5	0
39	Spectroscopic Investigation on the Origin of Photoinduced Carrier Generation in Semiconducting InGaO and InGaZnO Films. Journal of Physical Chemistry C, 2010, 114, 11962-11964.	3.1	14